Physics ICS Part 2 Chapter 18 Online MCQ's Test

Sr	Questions	Answers Choice
1	The circuit of full wave rectification consist of	A. Three diodes B. Four diodes C. Two diodes D. One diode
2	Photo diode is used for detection of.	A. Heat B. Magnet C. Current D. Light
3	For automatic Switching of streetlight, the op amplifier is used as.	A. Inductor B. Converter C. Comparator D. Thermistor
4	The input resistance of an op amplifier is.	A. Low B. High C. Zero D. Equal to output resistance
5	The use of LDR is in the circuit of.	A. Logic gate B. Rectifier C. Oscillator D. High Switch
6	In a transistor, collector current is controlled by:	A. Collector voltage B. Base current C. Collector resistance D. All of the above
7	The gain of transistor amplifier depends upon	A. Resistance connected with collector B. Resistance connected with base voltage C. Input voltage D. Output voltage
8	For normal transistor the emitter current can be given by	A. I_E = I_C B. I_E = I_C + I_B C. I_E = I_B D. None of these
9	_____ is the building block of every electronic circuit.	A. Semi conductor diode B. Resistor C. Capacitor D. Amplifier
10	NAND gate represented by:	A. X = A. B B. X = A+B C. X= A.B D. X=|A+B|
11	The impurity in the germinium is usually in the ratio of	A. 1:10⁶ B. 1:10⁴ C. 1:10⁸ D. 1:10¹⁰
12	Greater concentration of impurity is added in.	A. Base B. Emitter C. Collector D. LED
13	The gate, which changes the logic level to its opposite level is called	A. NOR gate B. AND gate C. OR gate D. NOT gate
14	The potential barrier for silicon is.	A. 0.7 V B. 0.5 V C. 0.3 V D. 0.9 V
		A. OR gate

15	X=A+B is the mathematical notation for.	B. NOR gate C. NAND gate D. AND gate
16	The output voltage of a rectifier is.	A. Smooth B. Pulsating C. Alternating D. Per featly direct
17	The term invertor is used for.	A. NOR gate B. XNOR gate C. NAND gate D. NOT gate
18	In a transistor, collector current is controlled by:	A. Collector voltage B. Base current C. Collector resistance D. All of the above
19	Rectification is the process of converting.	A. D.C. into A.C. B. A.C. in to D.C. C. Low signal to high D. High signal to low
20	The potential difference across depletion region in case of Si is	A. 0.6 volt B. 0.9 volt C. 0.7 volt D. 0.2 volt